## 09960441

```
1911
        (measur$4 near3 pressure) same (wafer substrate)
212
        (measur$4 near3 pressure) same (wafer substrate) same (capacit
$4)
29
        ((measur$4 near3 pressure) same (wafer substrate) same (capaci
t$4)) and 438/\$.ccls.
        (appl$4 near2 pressure near3 (wafer substrate)) same (measur$4
51
near3 pressure)
22
        (wafer substrate) same (measur$4 near3 pressure near3 processi
ng)
23
        (438/14.ccls. 438/15.ccls. 438/16.ccls. 438/17.ccls. 438/18.cc
ls.) and ((measur$4 near3 pressure) same (wafer substrate))
        (438/4.ccls. 438/5.ccls. 438/6.ccls. 438/7.ccls. 438/8.ccls. 4
38/10.ccls. 438/11.ccls. 438/12.ccls. 438/13.ccls.) and ((measur$4 nea
r3 pressure) same (wafer substrate))
23
        (capacit$4 near3 sens$4 near4 pressure near5 measur$4) same (w
afer substrate)
        (capacit$4 near3 pressure near2 sensor) and (pressure near3 da
ta near3 stor$3)
        (438/14.ccls. 438/15.ccls. 438/16.ccls. 438/17.ccls. 438/18.cc
ls.) and (pressure near2 sensor) and (pressure near3 data near3 stor$3
1
        (438/14.ccls. 438/15.ccls. 438/16.ccls. 438/17.ccls. 438/18.cc
ls.) and (pressure near3 data near3 stor$3)
        (438/14.ccls. 438/15.ccls. 438/16.ccls. 438/17.ccls. 438/18.cc
0
ls.) and ((measur$4 near3 pressure) same (stor$3 near3 data))
        (measur$4 near3 pressure) adj2 (on applied) adj2 (wafer substr
ate)
89
        ((measur$4 near3 pressure) same (wafer substrate)) and (sensor
near3 ((wafer substrate) near3 surface))
190
        430/50.ccls.
        430/51.ccls.
61
149
       430/52.ccls.
       430/53.ccls.
165
```